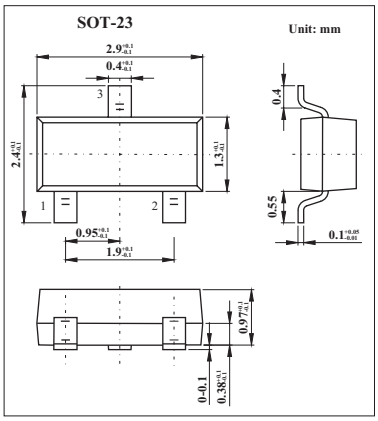
Schottky Barrier Diode

1SS366



■ Features

- Series connection of 2 elements in a very small-sized package facilitates high-density mounting and permits 1SS366-applied equipment to be made smaller.
- Small interterminal capacitance.
- Low forward voltage.
- High breakdown voltage.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	10	V
Forward Current	I_F	35	mA
Junction Temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_{F(1)}$	I_F = 1 mA	350		420	mV
	$V_{F(2)}$	I_F = 10 mA	480		580	mV
Forward Current	I_F	V_F = 1 V	35			mA
Reverse Current	$I_{R(1)}$	V_R = 2 V			0.2	μA
	$I_{R(2)}$	V_R = 10 V			10	μA
Interterminal Capacitance	C	V_R = 0 V, f = 1 MHz			0.85	pF
Forward Voltage Difference	$\triangle V_F$	I_F = 10 mA			10	mV
Interterminal Capacitance Difference	$\triangle C$	V_R = 0 V, f = 1 MHz			0.1	pF

■ Marking

Marking	FH